



US 20240215459A1

(19) **United States**

(12) **Patent Application Publication**
IWASAKI et al.

(10) **Pub. No.: US 2024/0215459 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **MEMORY DEVICE**

Publication Classification

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(51) **Int. Cl.**
H10N 50/85 (2006.01)
H10B 61/00 (2006.01)
H10N 50/20 (2006.01)

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(52) **U.S. Cl.**
CPC **H10N 50/85** (2023.02); **H10B 61/00** (2023.02); **H10N 50/20** (2023.02)

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(57) **ABSTRACT**

(21) Appl. No.: **18/476,628**

A memory device of embodiments includes a memory cell including: a first conductive layer; a second conductive layer; a third conductive layer provided between the first conductive layer and the second conductive layer; a variable resistance layer provided between the first conductive layer and the third conductive layer; and a switching layer provided between the third conductive layer and the second conductive layer. The switching layer contains an oxide of a first element, which is at least one element selected from a group consisting of zirconium, yttrium, tantalum, lanthanum, cerium, titanium, hafnium, and magnesium, and a compound of a second element that is at least one element selected from a group consisting of zinc, tin, gallium, indium, and bismuth and a third element that is at least one element selected from a group consisting of tellurium, sulfur, and selenium.

(22) Filed: **Sep. 28, 2023**

(30) **Foreign Application Priority Data**

Dec. 21, 2022 (JP) 2022-204150
Jul. 14, 2023 (JP) 2023-116214

